

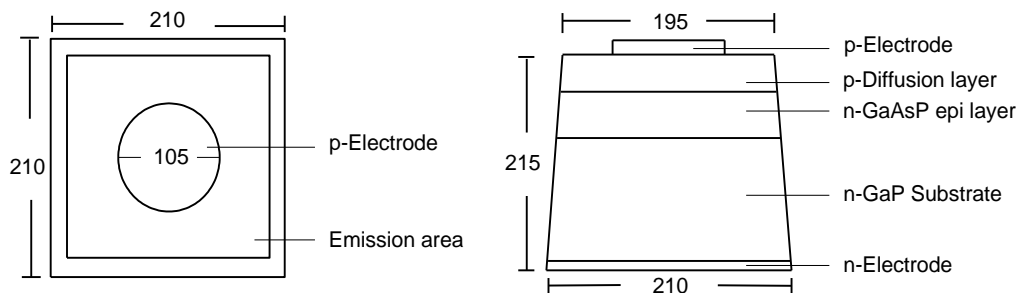
■ Features :

- GaAsP/ GaP Epi Wafer

■ Typical Applications :

- Lamp
- SMD
- Display

■ Outline Dimensions : (Unit: um)



■ Physical Structure :

Chip dimension	Chip size	210 um x 210 um
	Thickness	215 um
	Emission area	195 um
	Bonding pad	105 um
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

■ Electro-Optical Characteristics : (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	2.05	2.60	V
Reverse Current	I_R	$V_R = 5 \text{ V}$	-	-	10	μA
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	642	-	nm
	Hue		-	630	-	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	35	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	6.0	-	-	mcd

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

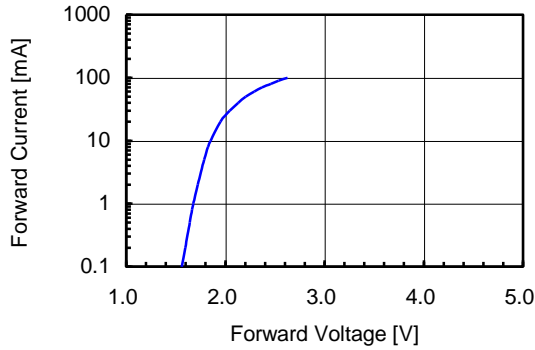


Fig 2. Relative Intensity vs. Forward Current

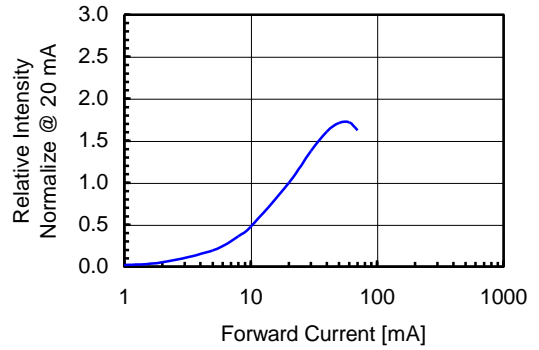


Fig 3. Forward Voltage vs. Temperature

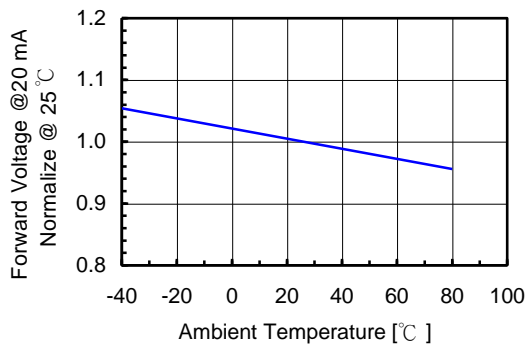


Fig 4. Relative Intensity vs. Temperature

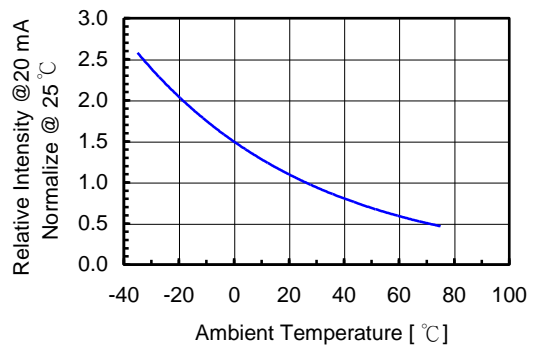


Fig 5. Relative Intensity vs. Wavelength

